2SA0914 (2SA914)

Silicon PNP epitaxial planar type

For audio system/pli drive Complementary to 2SC1953

■ Features

- A complementary pair with 2SC1953, is optimum for the predriver stage of a 60 W to 100 W output amplifier
- TO-126B package which requires no insulation plate for installation to the heat sink

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-150	V
Collector-emitter voltage (Base open)	V _{CEO}	-150	V
Emitter-base voltage (Collector open)	V _{EBO}	-5	V
Collector current	I_C	-50	mA
Peak collector current	I _{CP}	-100	mA
Collector power dissipation	P _C	1.2	W
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Unit: mm $8.0^{+0.5}_{-0.1}$ 3.2±0.2 ф 3.16±0.1 1. Emitter Collector 3: Base IO-126B-A1 Package

■ Electrical Characteristics $T_a = 25^{\circ}$ C

Emitter-base voltage (Collector open)	V_{EBO}	-5	V		— 10	0-126B-A	: Base 1 Package
Collector current	I_C	-50	mA		S		
Peak collector current	I _{CP}	-100	mA	•	11/10		
Collector power dissipation	P _C	1.2	W	S			
Junction temperature	Tj	150	°C	XO.	20		
Storage temperature	T _{stg}	-55 to +150	°C	, c'	O '		
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			2000	20			
■ Floatrical Characteristics T	2506	200	~\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\				
Peak collector current Collector power dissipation P _C 1.2 W Junction temperature T _j Storage temperature T _{stg} $-55 \text{ to} + 150$ $^{\circ}\text{C}$ Electrical Characteristics $T_a = 25^{\circ}\text{C} \pm 3^{\circ}\text{C}$							
Parameter	Symbo		Conditions C	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -100$	$\mu A I_B = 0$	-150			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_{\rm E} = -10 \mu$	$A, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	V _{CB} = -10	$00 \text{ V}, I_{\text{E}} = 0$			-1	μΑ
Forward current transfer ratio *	h_{FE}	$V_{CE} = -5$	$V_{\rm A}I_{\rm C} = -10 \text{ mA}$	130		330	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -30 \text{ m}$	$nA, I_B = -3 mA$			-1	V
Transition frequency	(F ₁)	$V_{CB} = -10$	$V, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$	70			MHz
Collector output capacitance	C_{ob}	$V_{CR} = -6$	$V, I_E = 0, f = 1 \text{ MHz}$			5	pF
	- 00	CB	· / L			_	r

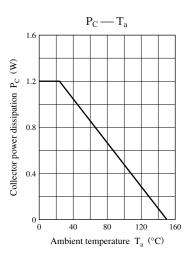
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

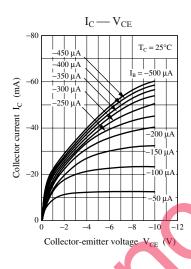
2. *: Rank classification

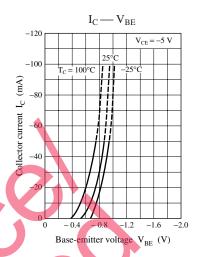
Rank	R	S
h_{FE}	130 to 220	185 to 330

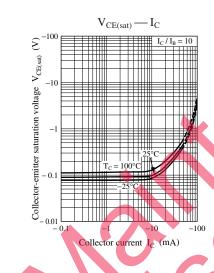
Note) The part number in the parenthesis shows conventional part number.

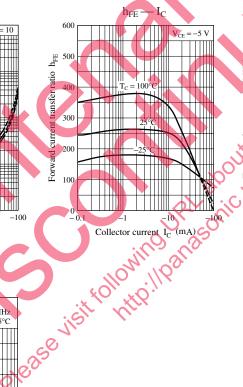
2SA0914 Panasonic

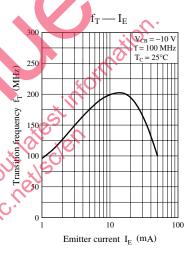


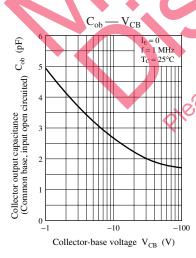












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